WANSEMI
万代半导体

WP2305AS3

Enhancement Mode P-Channel Power MOSFET

SOT23-3/PMOS/-17V/±12V/-0.65V/-5.5A/23mΩ

Rev0.7

-17V,23mΩ, -5.5A, P-Channel MOSFET

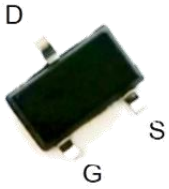
1.Features

- Advanced Trench Technology
- Surface mount package

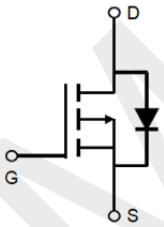
V_{DS}	$R_{DS(on)}$ Typ.	I_D.
-17V	23mΩ @ -4.5V	-5.5A
	29mΩ @ -2.5V	

2.Applications

- Power Management
- Load Switching



SOT23-3
Pin Description



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP2305AS3	2305A	SOT23-3	3,000	180,000

4.Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	-17	V
Gate to Source Voltage	V_{GSS}	±12	V
Drain Current (DC)	I_D	-5.5	A
Drain Current (Pulse), PW≤300μs	I_{DP}	-22	A
Total Dissipation	P_D	1.2	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5.Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	104	℃/W

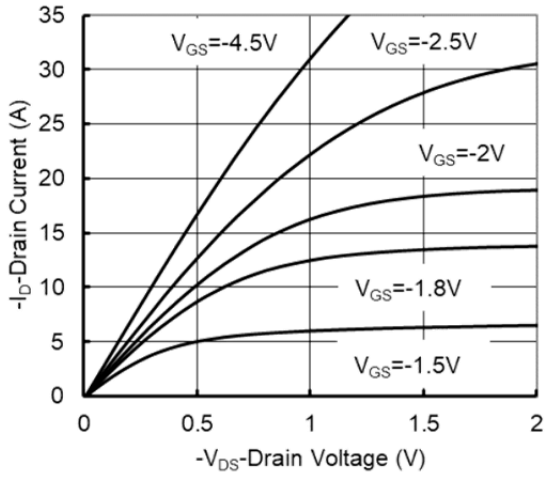
Note 2: When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25℃ (Note 3)

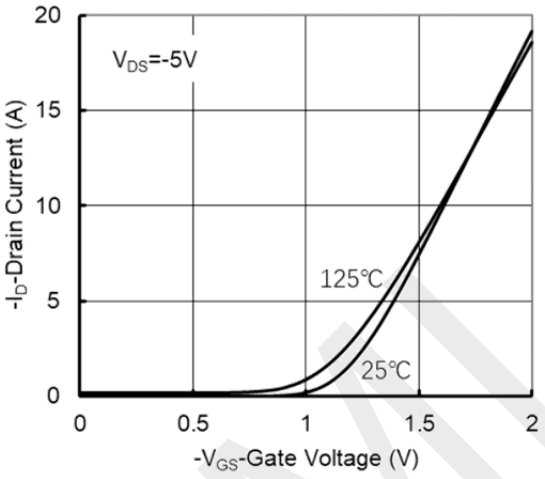
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = -250μA, V_{GS} = 0V	-17	-23		V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = -17V, V_{GS} = 0V			-1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±12V, V_{DS} = 0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=-250μA	-0.4	-0.65	-1.2	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	I_D =4A, V_{GS} =-4.5V		23	48	mΩ
		I_D =3A, V_{GS} = -2.5V		29	53	mΩ
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-10V, Frequency=1.0MHz		1010		pF
Output Capacitance	C_{oss}			130		pF
Reverse Transfer Capacitance	C_{rss}			109		pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DS} =-10V, R_L=2.5Ω,, R_G = 3Ω, V_{GEN} = -4.5V		8.5		ns
Rise Time	t_r			36		ns
Turn-OFF Delay Time	$t_{d(off)}$			77		ns
Fall Time	t_f			56		ns
Total Gate Charge	Q_g	V_{DS} = -10V, V_{GS} = -4.5V, I_D = -4A		11		nC
	Q_{gs}			2.2		nC
	Q_{gd}			2.5		nC
Diode Forward Voltage	V_{FSD}	I_S = 4A, V_{GS} = 0	-0.4	-0.85	-1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

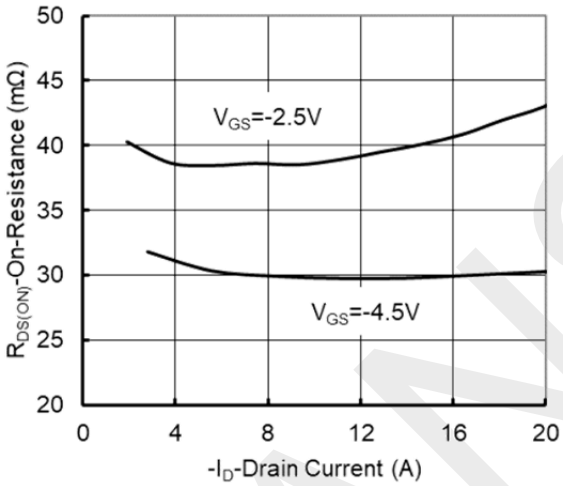
7.Typical Electrical and Thermal Characteristics



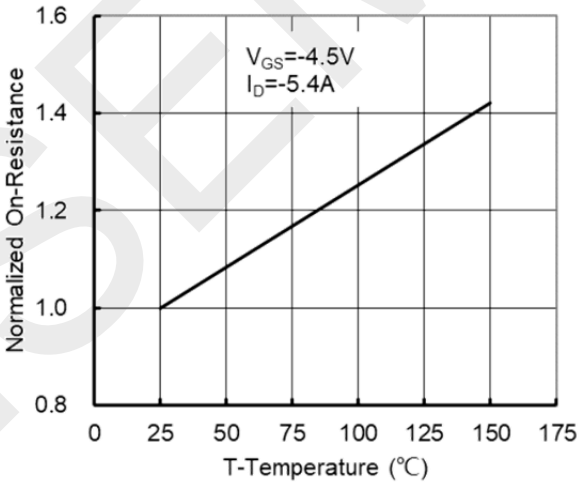
Output Characteristics



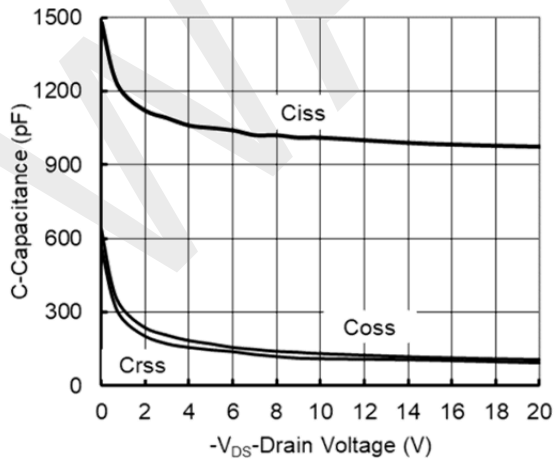
Transfer Characteristics



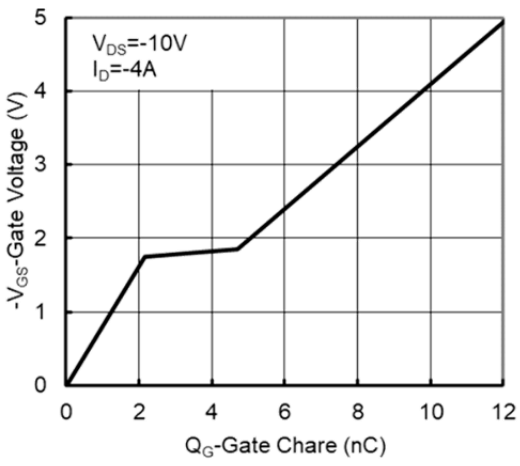
On-resistance vs. Drain Current



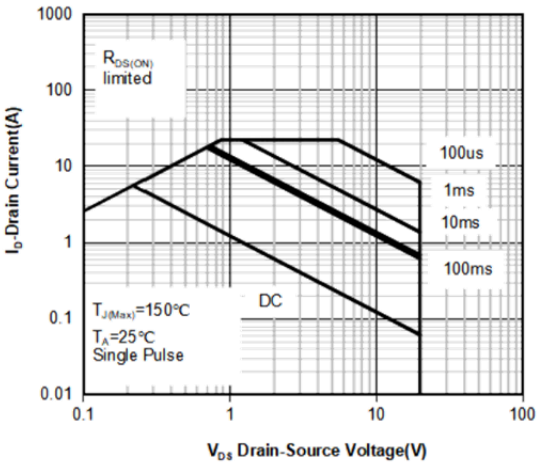
On-Resistance vs. Junction Temperature



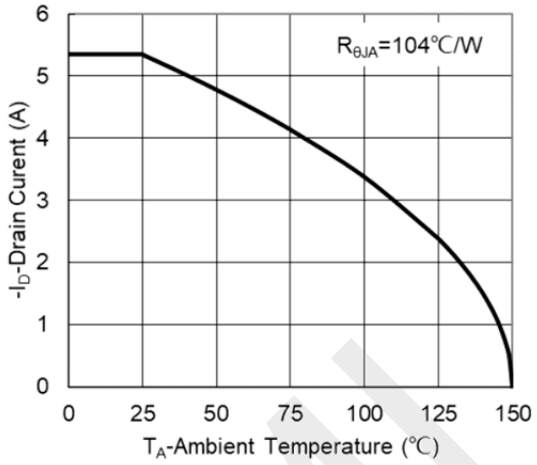
Capacitance Characteristics



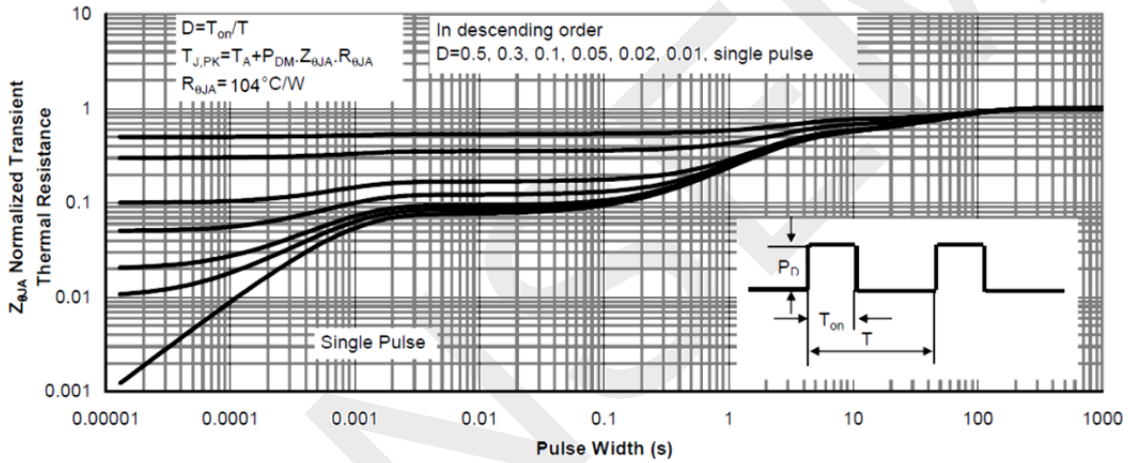
Gate Charge



Safe Operating Area

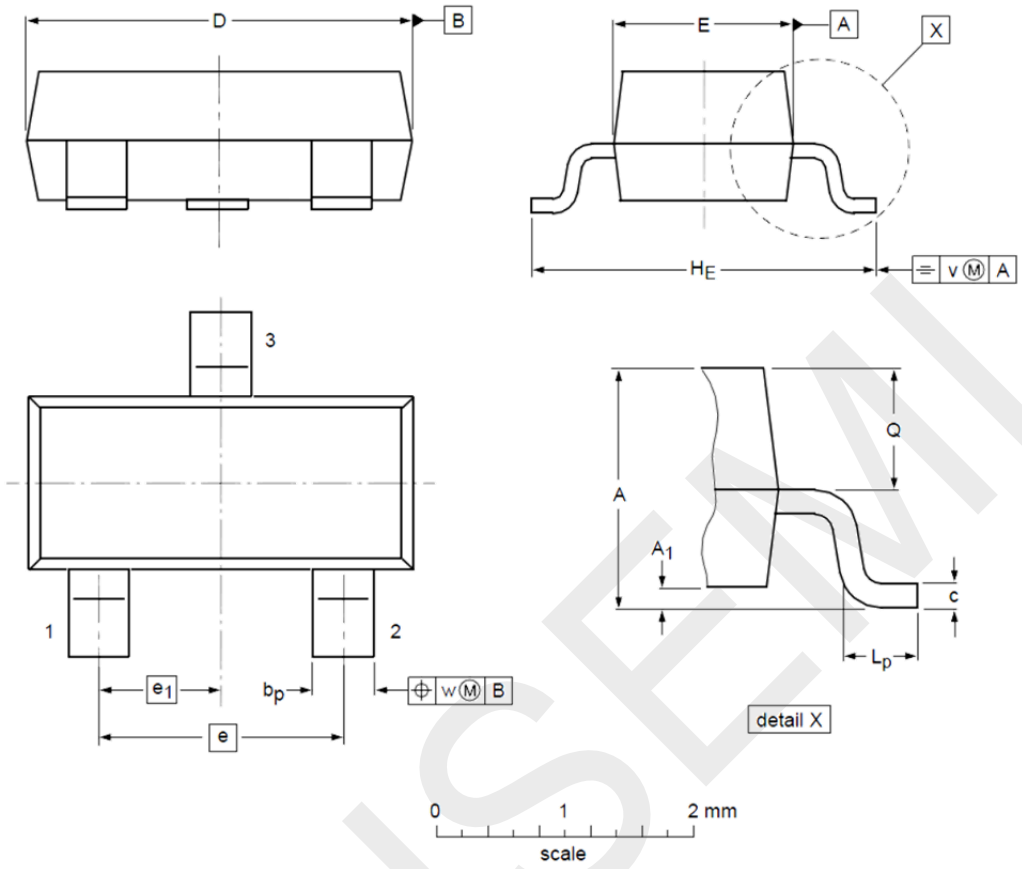


Maximum Continuous Drain Current vs. Ambient Temperature



Normalized Maximum Transient Thermal Impedance

8.Package Dimensions



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	1.00	1.17	1.30	**A_1**	0.01	0.05	0.10
b_p	0.35	0.39	0.50	**c**	0.10	0.20	0.26
D	2.70	2.90	3.10	**E**	1.30	1.58	1.70
e	--	1.90	--	**e_1**	--	0.95	--
H_E	2.50	2.78	3.00	**L_p**	0.20	0.32	0.60
Q	0.23	0.27	0.33	**v**	--	0.20	--
w	--	0.20	--				

9.Important Notice

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